

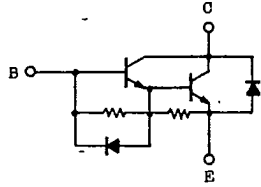
9097250 TOSHIBA (DISCRETE/OPTO)

90D 16279 DT-33-35

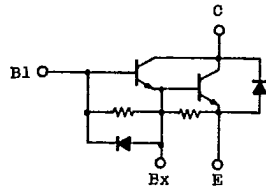


SEMICONDUCTOR
TECHNICAL DATA

MG200H1AL2
MG200H1FL1A

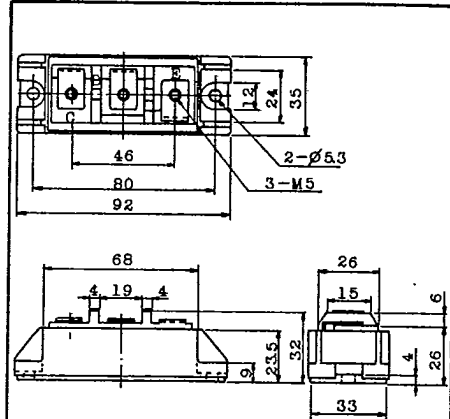


MG200H1AL2



MG200H1FL1

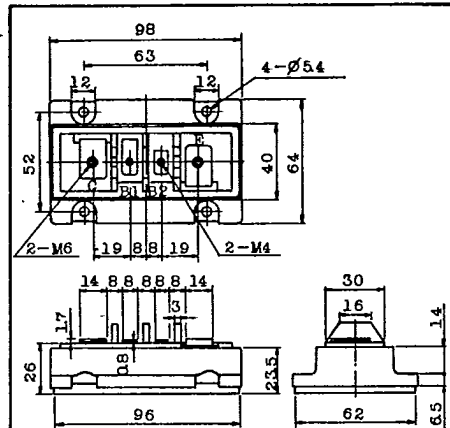
Unit in mm



JEDEC	-
EIAJ	-
TOSHIBA	2-68D1A

Weight : 210g

Unit in mm



JEDEC	-
EIAJ	-
TOSHIBA	2-98B1A

Weight : 420g

TOSHIBA CORPORATION

GT1A2A

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MAXIMUM RATINGS ($T_a=25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CB10}	600	V
Collector-Emitter Voltage	V_{CEO}	600	V
Collector-Emitter Sustaining Voltage	$V_{CEO(SUS)}$	550	V
Emitter-Base Voltage	V_{EB10}	6	V
Collector Current	DC	I_C	200
	lms	I_C	400
	DC	$-I_C$	200
Base Current	I_{B1}	8	A
Collector Power Dissipation ($T_c=25^\circ\text{C}$)	P_C	800	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-40~125	$^\circ\text{C}$
Isolation Voltage	V_{isol}	2500 (AC 1 Minute)	V
Screw Torque (Terminal M4/M6/Mounting)	-	20/30/30	kg·cm

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Collector Cut-off Current	I_{CB10}	$V_{CB1}=600\text{V}$, $I_E=0$	-	-	2.0	mA	
Emitter Cut-off Current	I_{EB10}	$V_{EB1}=6\text{V}$, $I_C=0$	-	-	400	mA	
Collector-Emitter Sustaining Voltage	$V_{CEO(SUS)}$	$I_C=0.5\text{A}$, $L=40\text{mH}$	550	-	-	V	
DC Current Gain	h_{FE}	$V_{CE}=5\text{V}$, $I_C=200\text{A}$	80	-	-		
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=200\text{A}$, $I_{B1}=6\text{A}$	-	-	2.0	V	
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		-	-	2.7	V	
Emitter-Collector Voltage	V_{ECO}	$I_E=200\text{A}$, $I_{B1}=0$	-	-	1.5	V	
Reverse Recovery Time	t_{rr}	$-I_C=200\text{A}$, $V_{EB1}=3\text{V}$ $V_{CE}=300\text{V}$	-	-	2.0	μs	
Collector Output Capacitance	C_{ob1}	$V_{CB1}=50\text{V}$, $I_E=0$ $f=1\text{MHz}$	-	1670	-	pF	
Switching Time	Turn-on Time		-	-	2.0	μs	
	Storage Time		t_{stg}	-	-		12
	Fall Time		t_f	$I_{B(1)}=-I_{B(2)}=6\text{A}$ DUTY CYCLE=0.5%	-		-
Thermal Resistance (Junction to Case)	$R_{th(j-c)}$	Transistor	-	-	0.156	$^\circ\text{C/W}$	
		Diode	-	-	0.65		

TOSHIBA CORPORATION

GT1A2A

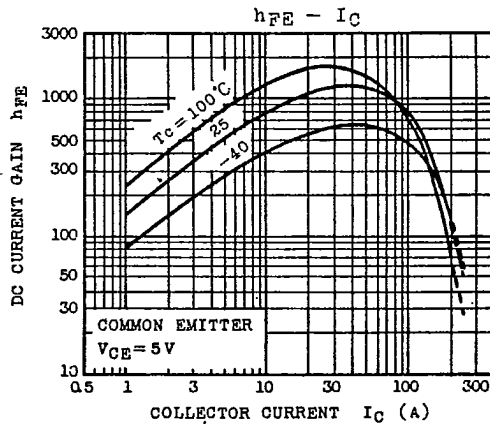
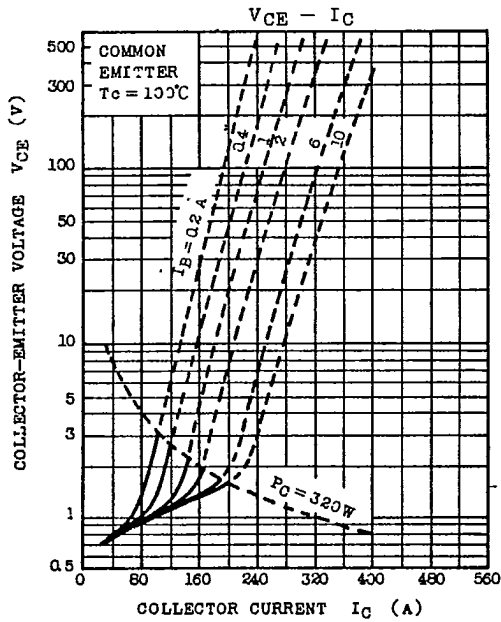
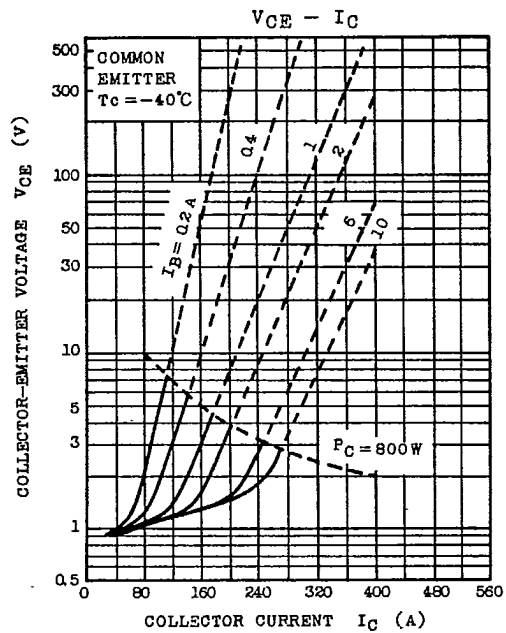
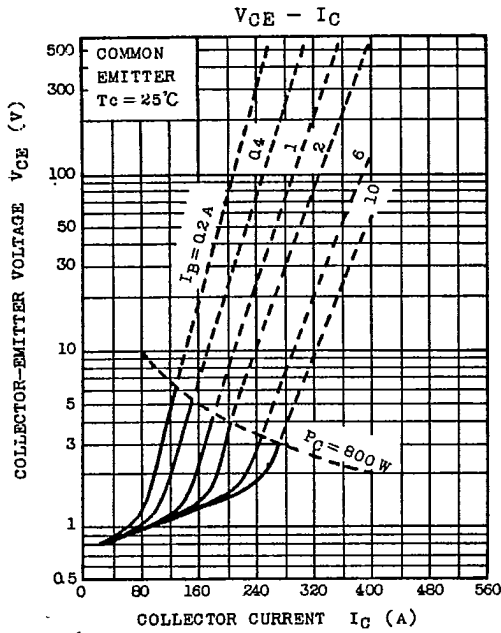
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TOSHIBA CORPORATION

GT1A2

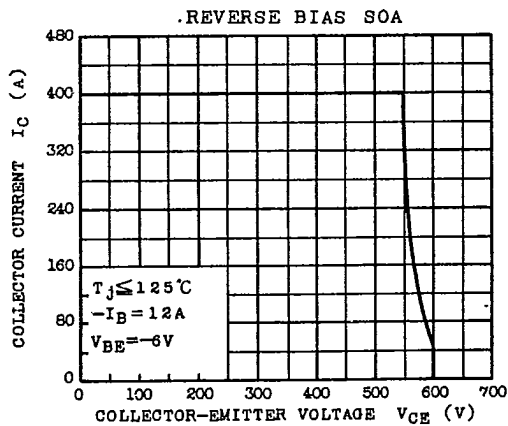
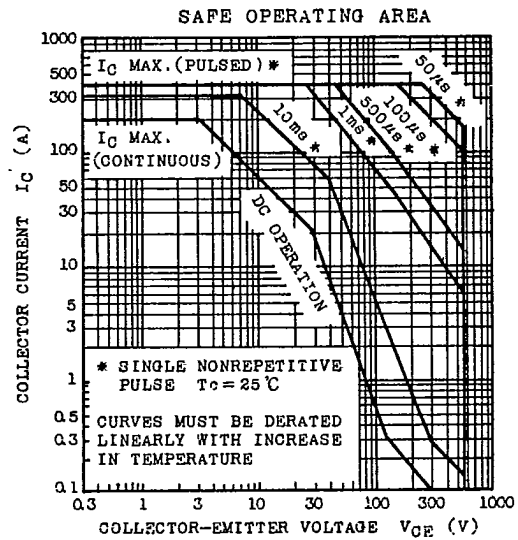
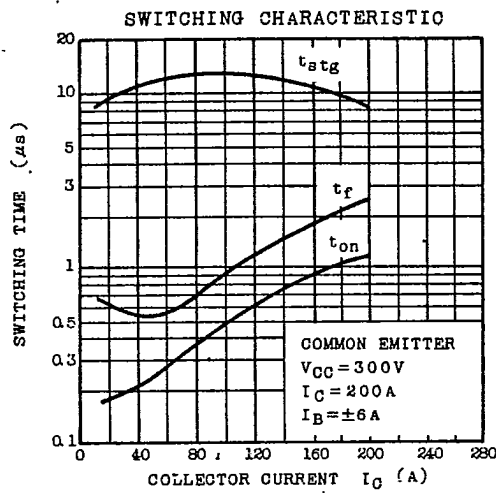
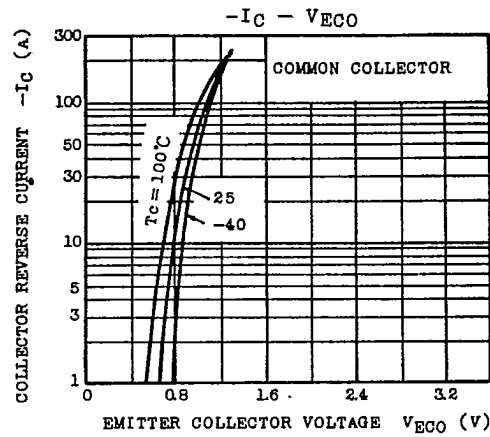
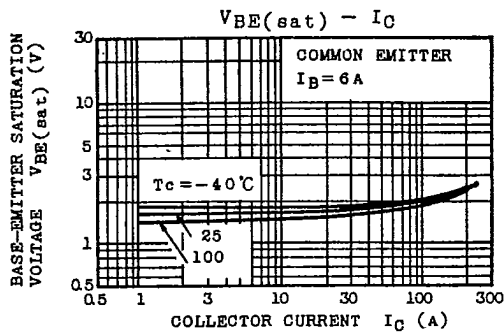
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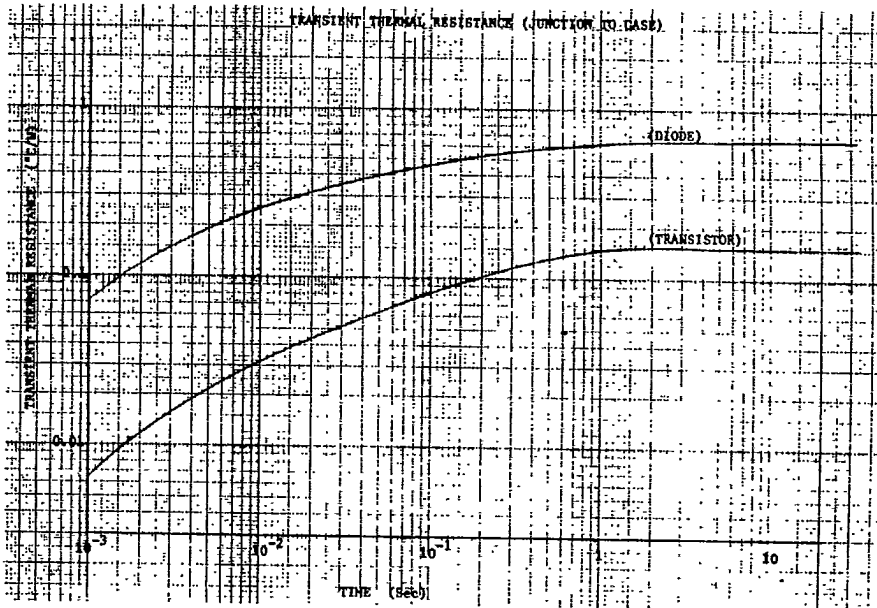
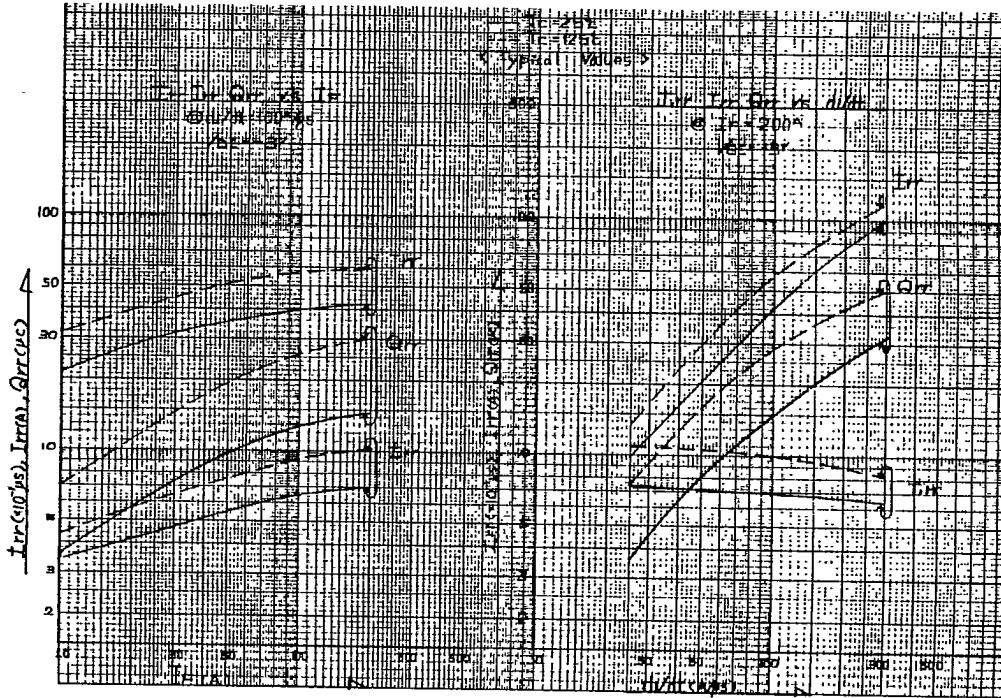
TOSHIBA CORPORATION

GT1A2



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TOSHIBA CORPORATION

GT1A2A